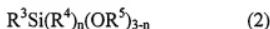


Amendments to the Claims:

1. (Currently amended) A composition for forming porous film, comprising a surfactant and a solution comprising polymer obtainable by hydrolyzing and condensing, in the presence of the surfactant, one or more alkoxy silanes represented by Formula (1) and one or more alkoxy silanes represented by Formula (2):



wherein R¹ represents a straight chain or branched alkyl group having 1 to 7 carbons or an aryl group wherein the alkyl or aryl group monovalent hydrocarbon group which may be substituted or non-substituted and when there are R¹'s, the R¹'s are independently the same or different; R² represents an alkyl group having 1 to 4 carbons and when there are R²'s, the R²'s are independently the same or different; R³ represents a straight chain or branched alkyl group having 8 to 30 carbons; R⁴ represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R⁴'s, the R⁴'s are independently the same or different; R⁵ represents an alkyl group having 1 to 4 carbons and when there are R⁵'s, the R⁵'s are independently the same or different; m is an integer of 0 to 3; and n is an integer of 0 to 2, wherein the one or more alkoxy silanes represented by Formula (1) comprise one or more tetraalkoxy silanes wherein m=0 and one or more alkoxy silanes wherein m=1, 2 or 3, and wherein said one or more alkoxy silanes represented by Formula (2) is present in an amount of 0.01 to 10 parts by weight to 100 parts by weight of said one or more alkoxy silanes represented by Formula (1).

2. (Original) The composition for forming porous film according to Claim 1 wherein said surfactant is a compound which decomposes, evaporates or sublimes when heated to 400°C or less.

3. (Canceled)

4. (Previously Presented) The composition for forming porous film according to Claim 1 wherein said one or more of the alkoxy silanes represented by Formula (1) is 10% by weight or more of tetraalkoxy silane.

5. (Previously Presented) The composition for forming porous film according to Claim 1, comprising a compound which is neutral at ordinary temperature and generates acid or alkali at 80 to 200°C.

6. (Previously Presented) A method for forming porous film comprising a step of applying said composition of Claim 1 on a substrate to form film and a step of transforming the film into porous film.

7. (Original) The method for forming porous film according to Claim 6 wherein said step of transforming comprises a step of drying said film and a step of removing said surfactant from the dried film.

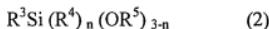
8. (Previously Presented) The method for forming porous film according to Claim 6 wherein said step of transforming comprises heating at 150 to 400°C.

9. (Previously Presented) A porous film obtainable from said composition of Claim 1.

10. (Previously Presented) An interlevel insulator film formable by said composition of Claim 1.

11. (Currently amended) A semiconductor device comprising internal porous film which is formable by a composition for forming porous film, comprising
a surfactant and
a solution comprising polymer obtainable by hydrolyzing and condensing, in the presence of the surfactant, one or more of alkoxy silane represented by Formula (1) and one or more of alkoxy silane represented by Formula (2):





wherein R^1 represents a straight chain or branched alkyl group having 1 to 7 carbons or an aryl group wherein the alkyl or aryl group monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^1 's, the R^1 's are independently the same or different; R^2 represents an alkyl group having 1 to 4 carbons and when there are R^2 's, the R^2 's are independently the same or different; R^3 represents a straight chain or branched alkyl group having 8 to 30 carbons; R^4 represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^4 's, the R^4 's are independently the same or different; R^5 represents an alkyl group having 1 to 4 carbons and when there are R^5 's, the R^5 's are independently the same or different; m is an integer of 0 to 3; and n is an integer of 0 to 2,

wherein the one or more alkoxy silanes represented by Formula (1) comprise one or more tetraalkoxy silanes wherein $m=0$ and one or more alkoxy silanes wherein $m=1, 2$ or 3 , and

wherein said one or more alkoxy silanes represented by Formula (2) is present in an amount of 0.01 to 10 parts by weight to 100 parts by weight of said one or more alkoxy silanes represented by Formula (1).

12. (Original) The semiconductor device according to Claim 11 wherein said surfactant is a compound which decomposes, evaporates or sublimes when heated to 400°C or less.

13. (Canceled)

14. (Previously Presented) The semiconductor device according to Claim 11 wherein said one or more of the alkoxy silanes represented by Formula (1) is 10% by weight or more of tetraalkoxy silane.

15. (Previously Presented) The semiconductor device according to Claim 11, comprising a compound which is neutral at ordinary temperature and generates acid or alkali at 80 to 200°C.

16. (Previously Presented) The semiconductor device according to Claim 11 wherein said porous film is between metal interconnections in a same layer of multi-level interconnects, or is between upper and lower metal interconnection layers.